Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Infineon Technologies
BSS209PW

For any questions, you can email us directly:
sales@integrated-circuit.com

Preliminary data

BSS 209PW

OptiMOS®-P Small-Signal-Transistor

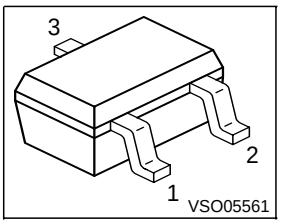
Feature

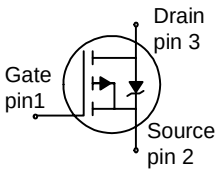
- P-Channel
- Enhancement mode
- Super Logic Level (2.5 V rated)
- 150°C operating temperature
- Avalanche rated
- d*v*/d*t* rated

Product Summary

V_{DS}	-20	V
$R_{DS(on)}$	550	mΩ
I_D	-0.58	A

SOT-323





Type	Package	Ordering Code	Marking
BSS 209PW	SOT-323	Q67042-S4074	X3s

Maximum Ratings,at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D		A
T_A=25°C		-0.58	
T_A=70°C		-0.46	
Pulsed drain current	$I_{D\ puls}$	-2.3	
T_A=25°C			
Avalanche energy, single pulse	E_{AS}	3.5	mJ
I_D=-0.58 A , V_{DD}=-10V, R_{GS}=25Ω			
Reverse diode d*v*/d*t*	d*v*/d*t*	-6	kV/µs
I_S=-0.58A, V_{DS}=-16V, d*i*/d*t*=200A/µs, T_{jmax}=150°C			
Gate source voltage	V_{GS}	±12	V
Power dissipation	P_{tot}	0.52	W
T_A=25°C			
Operating and storage temperature	T_j , T_{stg}	-55... +150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	120	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	240	
@ 6 cm^2 cooling area [1)]		-	-	160	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage V_{GS}=0V, I_D=-250µA	$V_{(BR)DSS}$	-20	-	-	V
Gate threshold voltage, V_{GS} = V_{DS} I_D=-3.5µA	$V_{GS(th)}$	-0.6	-0.9	-1.2	
Zero gate voltage drain current	I_{DSS}				µA
V_{DS}=-20V, V_{GS}=0, T_j=25°C		-	-0.1	-1	
V_{DS}=-20V, V_{GS}=0, T_j=150°C		-	-10	-100	
Gate-source leakage current V_{GS}=-12V, V_{DS}=0	I_{GSS}	-	-10	-100	nA
Drain-source on-state resistance V_{GS}=-2.5V, I_D=-0.46A	$R_{DS(on)}$	-	563	900	mΩ
Drain-source on-state resistance V_{GS}=-4.5, I_D=-0.58A	$R_{DS(on)}$	-	369	550	

[1]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air; t≤10 sec.

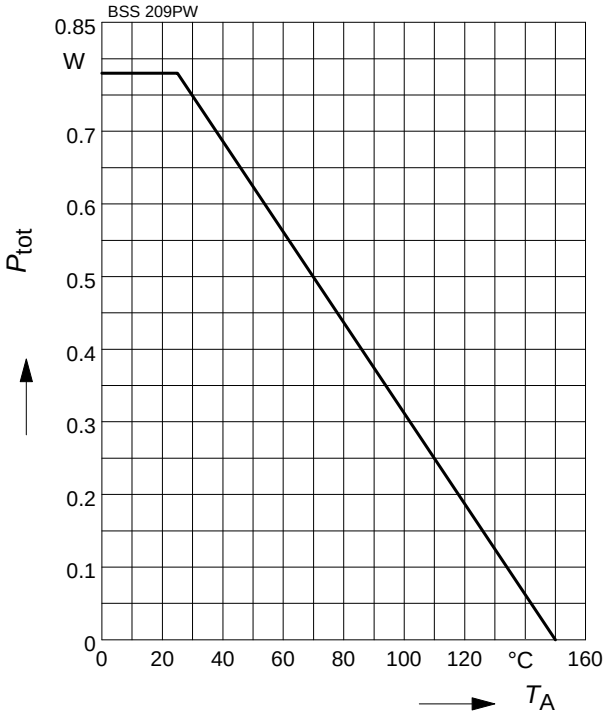
Preliminary data **BSS 209PW**

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic Characteristics						
Transconductance	g_{fs}	$\lvert V_{DS}\rvert \geq 2 * \lvert I_D\rvert * R_{DS(on)max}$, I_D=-0.46A	0.87	1.74	-	S
Input capacitance	C_{iss}	V_{GS}=0, V_{DS}=-15V, f=1MHz	-	89.9	-	pF
Output capacitance	C_{oss}		-	40.1	-	
Reverse transfer capacitance	C_{rss}		-	31.5	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-10V, V_{GS}=-4.5V, I_D=-0.58A, R_G=6Ω	-	4.4	6.6	ns
Rise time	t_r		-	5.8	8.7	
Turn-off delay time	$t_{d(off)}$		-	7.6	11.4	
Fall time	t_f		-	4.5	6.7	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=-10V, I_D=-0.58A	-	-0.12	-0.17	nC
Gate to drain charge	Q_{gd}		-	-0.74	-1.1	
Gate charge total	Q_g	V_{DD}=-10V, I_D=-0.58A, V_{GS}=0 to -4.5V	-	-0.92	-1.38	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=-10V, I_D=-0.58A	-	-1.7	-	V
Reverse Diode						
Inverse diode continuous forward current	I_S	T_A=25°C	-	-	-0.5	A
Inverse diode direct current, pulsed	I_{SM}		-	-	-2.3	
Inverse diode forward voltage	V_{SD}	V_{GS}=0, $\lvert I_F\rvert = \lvert I_D\rvert$	-	-1.3	-0.88	V
Reverse recovery time	t_{rr}	V_R=-10V, $\lvert I_F\rvert = \lvert I_D\rvert$, di_F/dt=100A/µs	-	9	11.2	ns
Reverse recovery charge	Q_{rr}		-	1.27	1.59	nC

1 Power dissipation

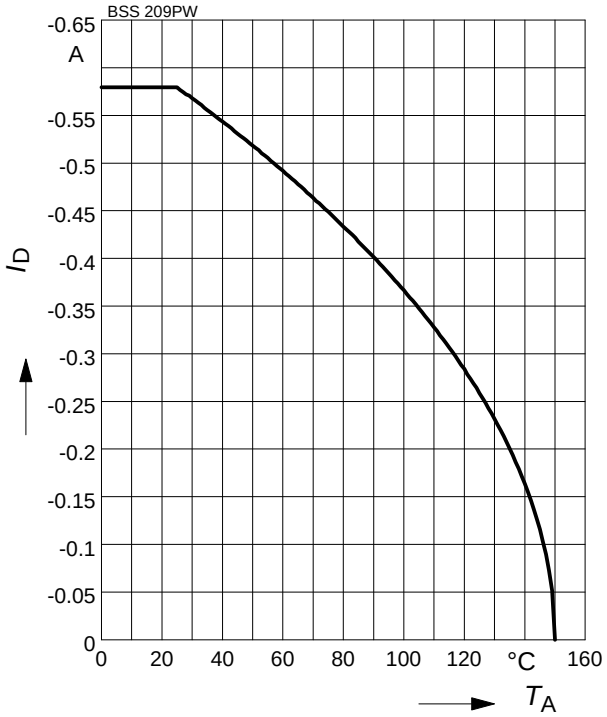
$P_{tot} = f(T_A)$



2 Drain current

$I_D = f(T_A)$

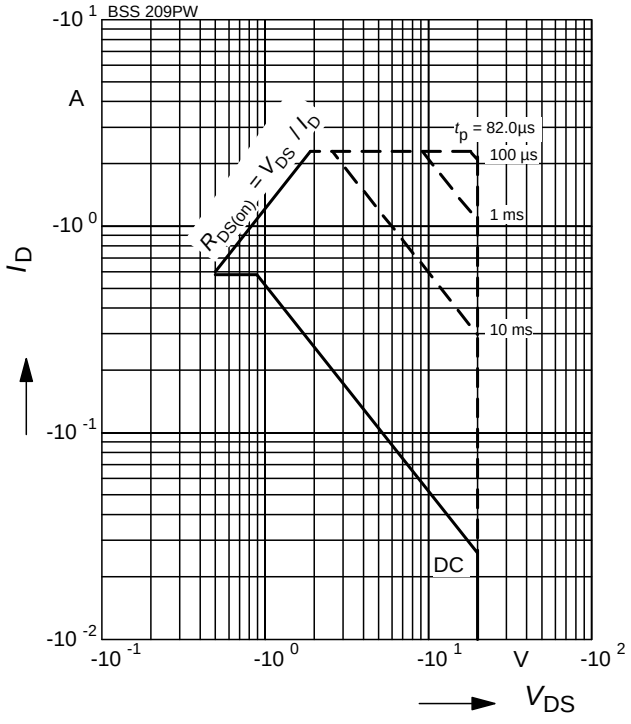
parameter: $|V_{GS}| \geq 4.5$ V



3 Safe operating area

$I_D = f(V_{DS})$

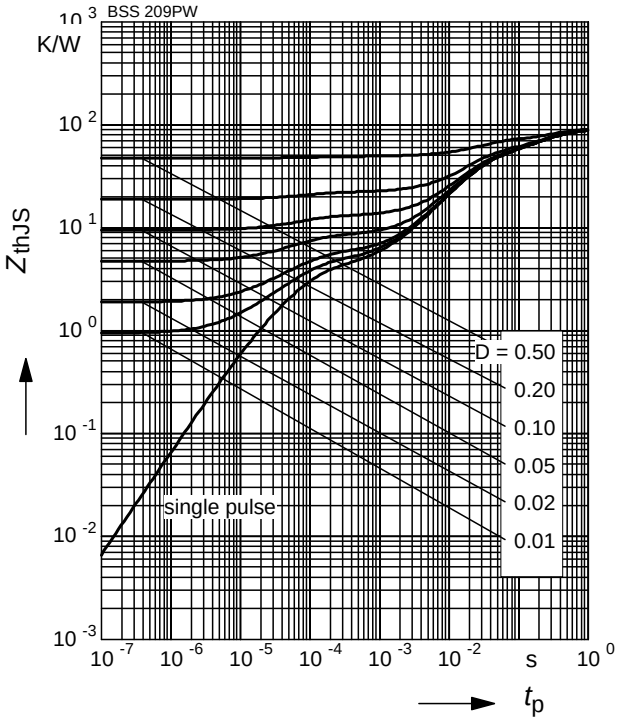
parameter : $D = 0$, $T_A = 25$ °C



4 Transient thermal impedance

$Z_{thJS} = f(t_p)$

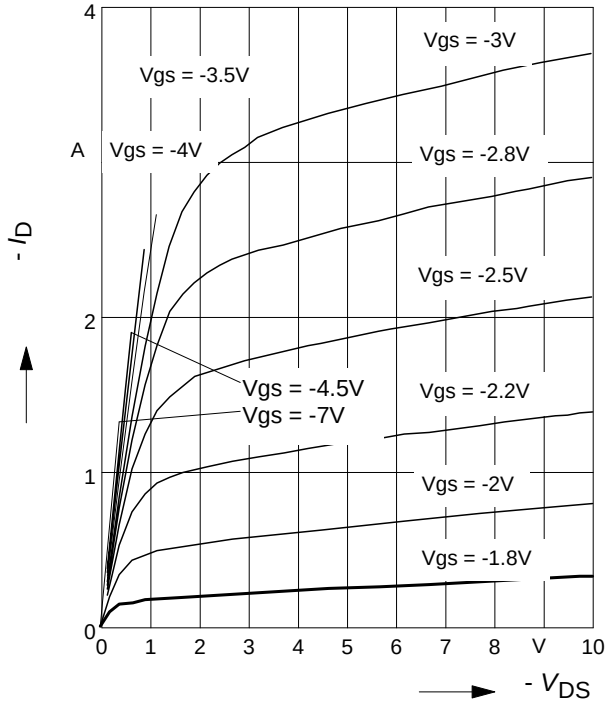
parameter : $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

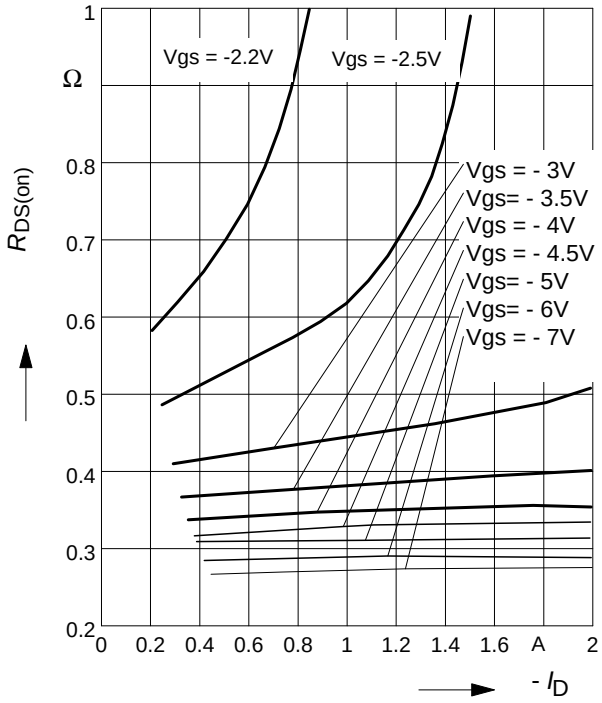
parameter: t_p = 80 µs



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

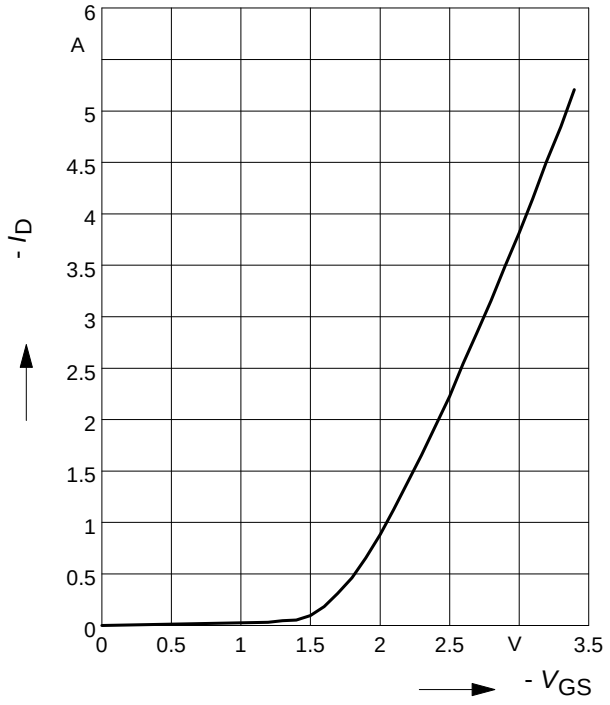
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $|V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

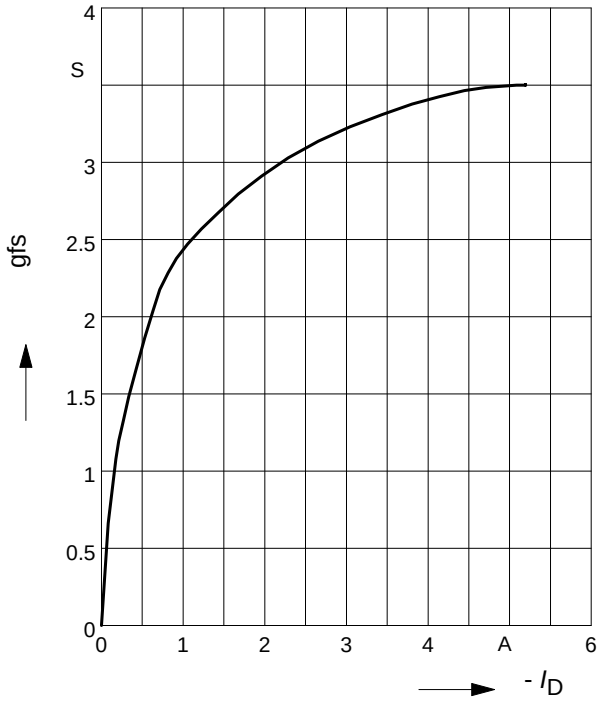
parameter: t_p = 80 µs



8 Typ. forward transconductance

g_{fs} = f(I_D); T_j=25°C

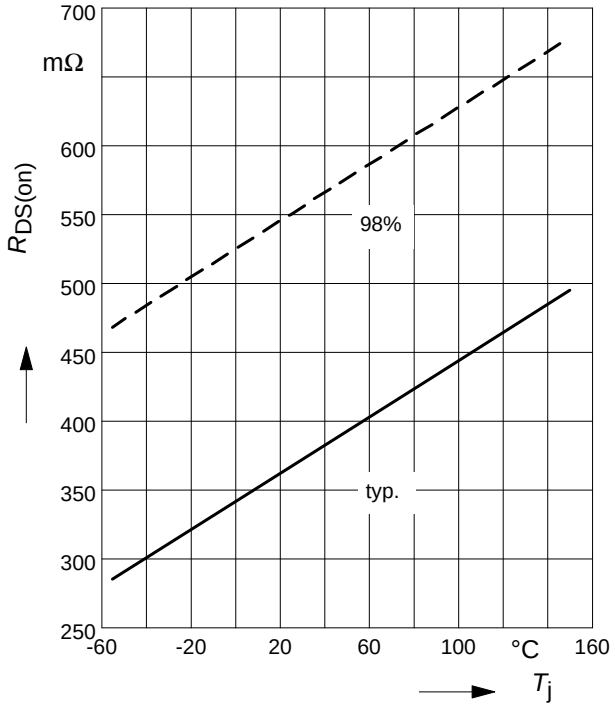
parameter: t_p = 80 µs



9 Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

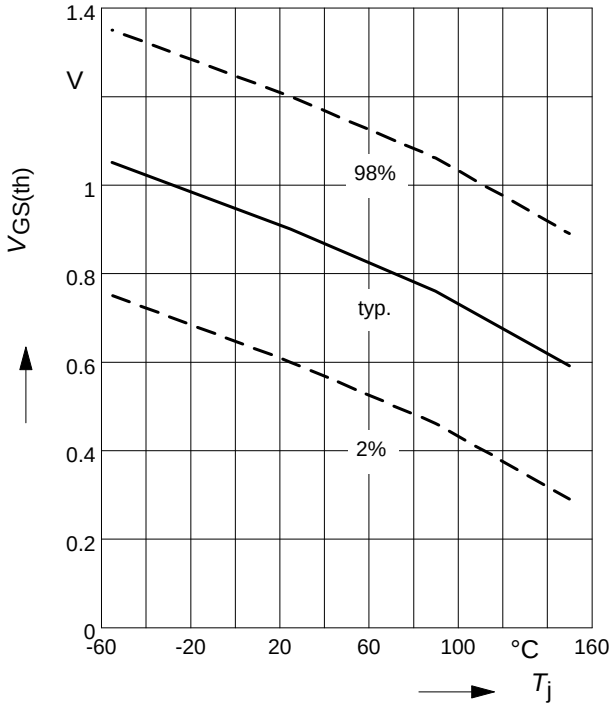
parameter: I_D = -0.58 A, V_{GS} = -4.5 V



10 Gate threshold voltage

$V_{GS(th)} = f(T_j)$

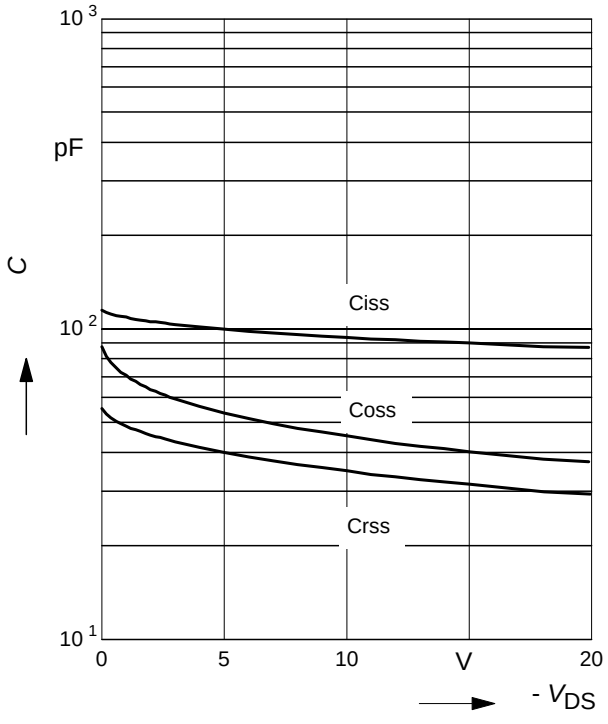
parameter: $V_{GS} = V_{DS}$, I_D = -3.5 µA



11 Typ. capacitances

$C = f(V_{DS})$

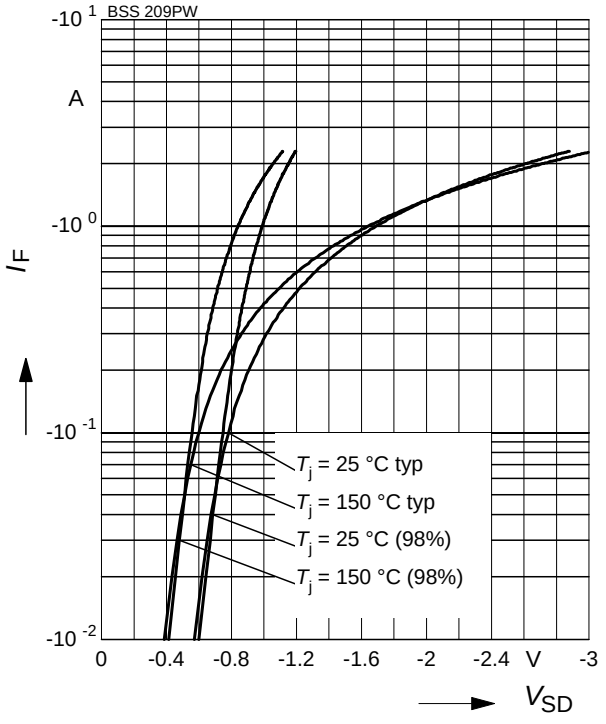
parameter: V_{GS}=0, f=1 MHz



12 Forward character. of reverse diode

$I_F = f(V_{SD})$

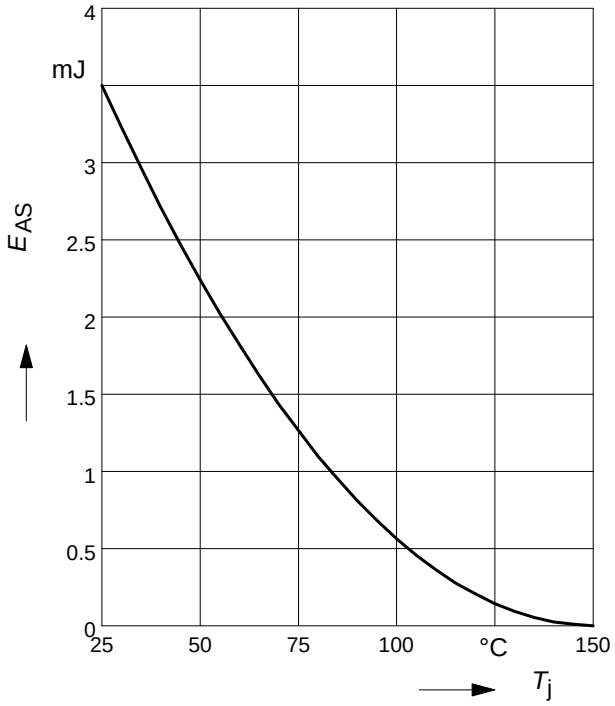
parameter: T_j , tp = 80 µs



13 Typ. avalanche energy

$E_{AS} = f(T_j)$, par.: I_D = -0.58 A

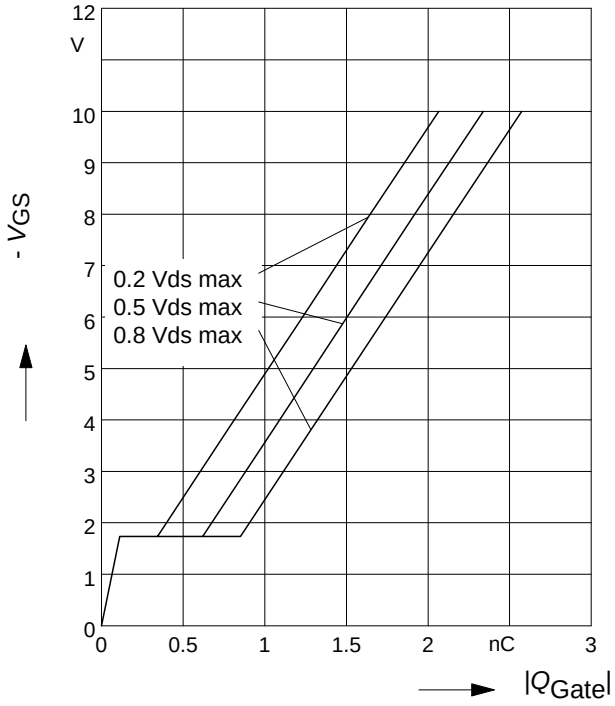
V_{DD} = -10 V, R_{GS} = 25 Ω



14 Typ. gate charge

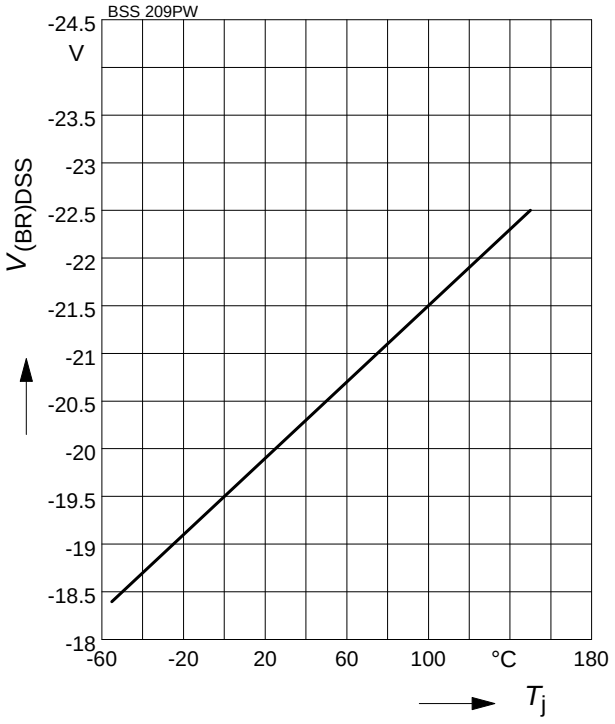
$|V_{GS}| = f(Q_{Gate})$

parameter: I_D = -0.58 A pulsed



15 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München

Attention please!
The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information
For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Reprensatives worldwide (see address list).

Warnings
Due to technical requirements components may contain dangerous substances.
For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.